

February 1988

CD4023BM/CD4023BC Buffered Triple 3-Input NAND Gate

CD4025BM/CD4025BC Buffered Triple 3-Input NOR Gate

General Description

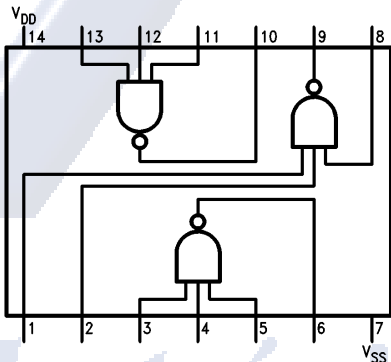
These triple gates are monolithic complementary MOS (CMOS) integrated circuits constructed with N- and P-channel enhancement mode transistors. They have equal source and sink current capabilities and conform to standard B series output drive. The devices also have buffered outputs which improve transfer characteristics by providing very high gain. All inputs are protected against static discharge with diodes to V_{DD} and V_{SS} .

Features

- Wide supply voltage range 3.0V to 15V
- High noise immunity $0.45 V_{DD}$ (typ.)
- Low power TTL compatibility fan out of 2 driving 74L or 1 driving 74LS
- 5V–10V–15V parametric ratings
- Symmetrical output characteristics
- Maximum input leakage $1 \mu A$ at 15V over full temperature range

Connection Diagrams

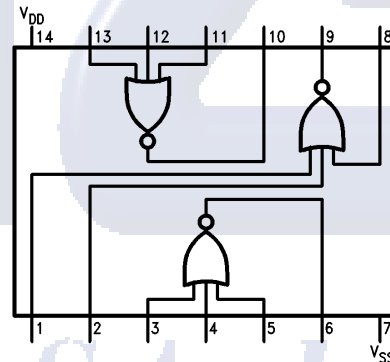
CD4023BM/CD4023BC
Dual-In-Line Package



Top View

TL/F/5956-1

CD4025BM/CD4025BC
Dual-In-Line Package



Top View

TL/F/5956-2

Order Number CD4023B or CD4025B

CD4023BM/CD4023BC Buffered Triple 3-Input NAND Gate
CD4025BM/CD4025BC Buffered Triple 3-Input NOR Gate

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

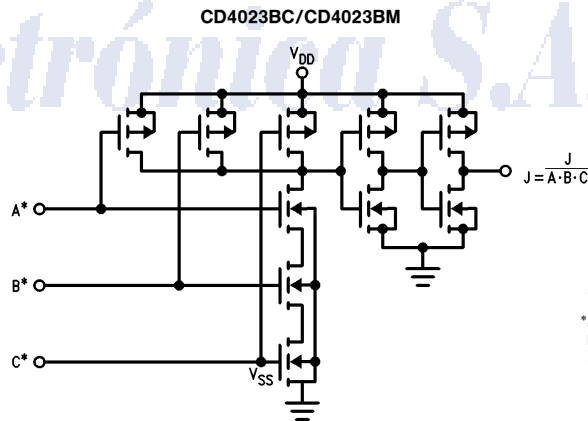
DC Supply Voltage (V_{DD})	$-0.5 V_{DC}$ to $+18 V_{DC}$
Input Voltage (V_{IN})	$-0.5 V_{DC}$ to $V_{DD} + 0.5 V_{DC}$
Storage Temp. Range (T_S)	-65°C to $+150^{\circ}\text{C}$
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (T_L)	
(Soldering, 10 seconds)	260°C

Recommended Operating Conditions

DC Supply Voltage (V_{DD})	$5 V_{DC}$ to $15 V_{DC}$
Input Voltage (V_{IN})	$0 V_{DC}$ to $V_{DD} V_{DC}$
Operating Temperature Range (T_A)	
CD4023BM, CD4025BM	-55°C to $+125^{\circ}\text{C}$
CD4023BC, CD4025BC	-40°C to $+85^{\circ}\text{C}$

DC Electrical Characteristics CD4023BM, CD4025BM (Note 2)

Symbol	Parameter	Conditions	-55°C		$+25^{\circ}\text{C}$			$+125^{\circ}\text{C}$		Units
			Min	Typ	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5\text{V}$		0.25		0.004	0.25		7.5	μA
		$V_{DD} = 10\text{V}$		0.5		0.005	0.5		15	μA
		$V_{DD} = 15\text{V}$		1.0		0.006	1.0		30	μA
V_{OL}	Low Level Output Voltage	$V_{DD} = 5\text{V}$		0.05		0	0.05		0.05	V
		$V_{DD} = 10\text{V}$		0.05		0	0.05		0.05	V
		$V_{DD} = 15\text{V}$		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$V_{DD} = 5\text{V}$	4.95		4.95	5		4.95		V
		$V_{DD} = 10\text{V}$	9.95		9.95	10		9.95		V
		$V_{DD} = 15\text{V}$	14.95		14.95	15		14.95		V
V_{IL}	Low Level Input Voltage	$V_{DD} = 5\text{V}, V_O = 4.5\text{V}$		1.5		2	1.5		1.5	V
		$V_{DD} = 10\text{V}, V_O = 9.0\text{V}$		3.0		4	3.0		3.0	V
		$V_{DD} = 15\text{V}, V_O = 13.5\text{V}$		4.0		6	4.0		4.0	V
V_{IH}	High Level Input Voltage	$V_{DD} = 5\text{V}, V_O = 0.5\text{V}$	3.5		3.5	3		3.5		V
		$V_{DD} = 10\text{V}, V_O = 1.0\text{V}$	7.0		7.0	6		7.0		V
		$V_{DD} = 15\text{V}, V_O = 1.5\text{V}$	11.0		11.0	9		11.0		V
I_{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5\text{V}, V_O = 0.4\text{V}$	0.64		0.51	0.88		0.36		mA
		$V_{DD} = 10\text{V}, V_O = 0.5\text{V}$	1.6		1.3	2.2		0.90		mA
		$V_{DD} = 15\text{V}, V_O = 1.5\text{V}$	4.2		3.4	8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{DD} = 5\text{V}, V_O = 4.6\text{V}$	-0.64		-0.51	-0.88		-0.36		mA
		$V_{DD} = 10\text{V}, V_O = 9.5\text{V}$	-1.6		-1.3	-2.2		-0.90		mA
		$V_{DD} = 15\text{V}, V_O = 13.5\text{V}$	-4.2		-3.4	-8		-2.4		mA
I_{IN}	Input Current	$V_{DD} = 15\text{V}, V_{IN} = 0\text{V}$		-0.10		-10^{-5}	-0.10		-1.0	μA
		$V_{DD} = 15\text{V}, V_{IN} = 15\text{V}$		0.10		10^{-5}	0.10		1.0	μA

Schematic Diagram

$\frac{1}{3}$ Device Shown

*All Inputs Protected by Standard CMOS Input Protection Circuit.

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DC Electrical Characteristics CD4023BC, CD4025BC (Note 2)

Symbol	Parameter	Conditions	-40°C		+25°C			+85°C		Units
			Min	Typ	Min	Typ	Max	Min	Max	
I _{DD}	Quiescent Device Current	V _{DD} = 5V		1.0		0.004	1.0		7.5	μA
		V _{DD} = 10V		2.0		0.005	2.0		15	μA
		V _{DD} = 15V		4.0		0.006	4.0		30	μA
V _{OL}	Low Level Output Voltage	V _{DD} = 5V		0.05		0	0.05		0.05	V
		V _{DD} = 10V		0.05		0	0.05		0.05	V
		V _{DD} = 15V		0.05		0	0.05		0.05	V
V _{OH}	High Level Output Voltage	V _{DD} = 5V	4.95		4.95	5		4.95		V
		V _{DD} = 10V	9.95		9.95	10		9.95		V
		V _{DD} = 15V	14.95		14.95	15		14.95		V
V _{IL}	Low Level Input Voltage	V _{DD} = 5V, V _O = 4.5V	I _O < 1 μA	1.5		2	1.5		1.5	V
		V _{DD} = 10V, V _O = 9.0V		3.0		4	3.0		3.0	V
		V _{DD} = 15V, V _O = 13.5V		4.0		6	4.0		4.0	V
V _{IH}	High Level Input Voltage	V _{DD} = 5V, V _O = 0.5V	I _O < 1 μA	3.5		3.5	3		3.5	V
		V _{DD} = 10V, V _O = 1.0V		7.0		7.0	6		7.0	V
		V _{DD} = 15V, V _O = 1.5V		11.0		11.0	9		11.0	V
I _{OL}	Low Level Output Current (Note 3)	V _{DD} = 5V, V _O = 0.4V	0.52		0.44	0.88		0.36		mA
		V _{DD} = 10V, V _O = 0.5V	1.3		1.1	2.2		0.90		mA
		V _{DD} = 15V, V _O = 1.5V	3.6		3.0	8		2.4		mA
I _{OH}	High Level Output Current (Note 3)	V _{DD} = 5V, V _O = 4.6V	-0.52		-0.44	-0.88		-0.36		mA
		V _{DD} = 10V, V _O = 9.5V	-1.3		-1.1	-2.2		-0.90		mA
		V _{DD} = 15V, V _O = 13.5V	-3.6		-3.0	-8		-2.4		mA
I _{IN}	Input Current	V _{DD} = 15V, V _{IN} = 0V		-0.3		-10 ⁻⁵	-0.3		-1.0	μA
		V _{DD} = 15V, V _{IN} = 15V		0.3		10 ⁻⁵	0.3		1.0	μA

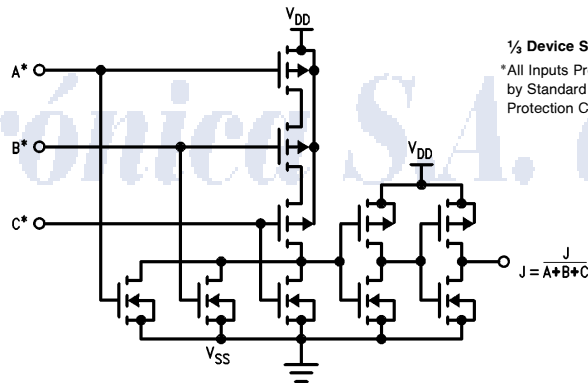
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2: V_{SS} = 0V unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

Schematic Diagram

CD4025BM/CD4025BC

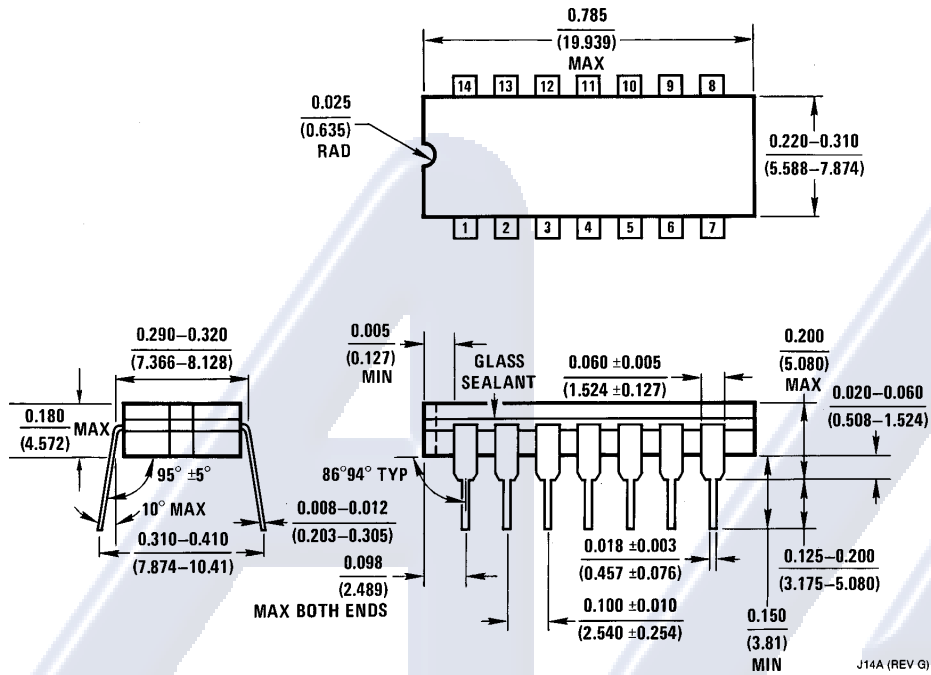


TL/F/5956-4

AC Electrical Characteristics* $T_A = 25^\circ\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}$, unless otherwise specified									
Symbol	Parameter	Conditions	CD4023BC CD4023BM			CD4025BC CD4025BM			Units
			Min	Typ	Max	Min	Typ	Max	
t_{PHL}	Propagation Delay, High-to-Low Level	$V_{\text{DD}} = 5\text{V}$		130	250		130	250	ns
		$V_{\text{DD}} = 10\text{V}$		60	100		60	100	ns
		$V_{\text{DD}} = 15\text{V}$		40	70		40	70	ns
t_{PLH}	Propagation Delay, Low-to-High Level	$V_{\text{DD}} = 5\text{V}$		110	250		120	250	ns
		$V_{\text{DD}} = 10\text{V}$		50	100		60	100	ns
		$V_{\text{DD}} = 15\text{V}$		35	70		40	70	ns
t_{THL} , t_{TLH}	Transition Time	$V_{\text{DD}} = 5\text{V}$		90	200		90	200	ns
		$V_{\text{DD}} = 10\text{V}$		50	100		50	100	ns
		$V_{\text{DD}} = 15\text{V}$		40	80		40	80	ns
C_{IN}	Average Input Capacitance	Any Input		5	7.5		5	7.5	pF
C_{PD}	Power Dissipation Capacity (Note 4)	Any Gate		17			17		pF

*AC Parameters are guaranteed by DC correlated testing.

Note 4: C_{PD} determines the no load AC power consumption of any CMOS device. For complete explanation, see 54C/74C Family Characteristics Application Note AN-90.

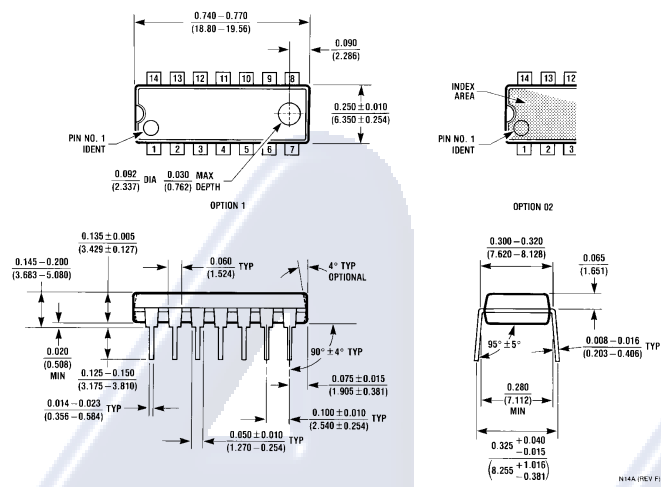
Physical Dimensions inches (millimeters)

Ceramic Dual-In-Line Package (J)
 Order Number CD4023BMJ, CD4023BCJ, CD4025BMJ or CD4025BCJ
 NS Package Number J14A

J14A (REV G)

CD4023BM/CD4023BC Buffered Triple 3-Input NAND Gate
CD4025BM/CD4025BC Buffered Triple 3-Input NOR Gate

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N)
Order Number CD4023BMN, CD4023BCN, CD4025BMN or CD4025BCN
NS Package Number N14A

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 National Semiconductor Corporation 1111 West Bardin Road Arlington, TX 76017 Tel: 1(800) 272-9959 Fax: 1(800) 737-7018	National Semiconductor Europe Fax: (+49) 0-180-530 85 86 Email: cnjwge@tevm2.nsc.com Deutsch Tel: (+49) 0-180-530 85 85 English Tel: (+49) 0-180-532 78 32 Français Tel: (+49) 0-180-532 93 58 Italiano Tel: (+49) 0-180-534 16 80	National Semiconductor Hong Kong Ltd. 13th Floor, Straight Block, Ocean Centre, 5 Canton Rd. Tsimshatsui, Kowloon Hong Kong Tel: (852) 2737-1600 Fax: (852) 2736-9960	National Semiconductor Japan Ltd. Tel: 81-043-299-2309 Fax: 81-043-299-2408
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